

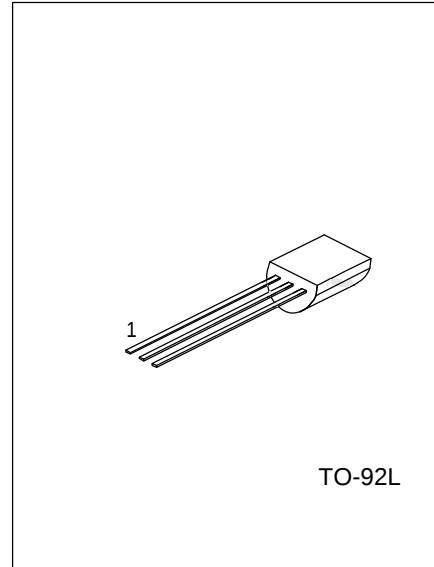
UTC A928A PNP EPITAXIAL SILICON TRANSISTOR

AUDIO POWER AMPLIFIER

FEATURES

*Collector Dissipation $P_c=1$ Watt

*3 Watt Output Application



1:EMITTER 2: COLLECTOR 3: BASE

ABSOLUTE MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$,unless otherwise specified)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CB0}	-30	V
Collector-emitter voltage	V_{CE0}	-30	V
Emitter-base voltage	V_{EB0}	-5	V
Collector dissipation	P_c	1	W
Collector current	I_c	-2	A
Junction Temperature	T_j	150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55 ~ +150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS($T_a=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	BV_{CB0}	$I_c=-100\mu\text{A}, I_E=0$	-30			V
Collector-emitter breakdown voltage	BV_{CE0}	$I_c=-10\text{mA}, I_B=0$	-30			V
Emitter-base breakdown voltage	BV_{EB0}	$I_E=-1\text{mA}, I_c=0$	-5			V
Collector cut-off current	I_{CB0}	$V_{CB}=-30\text{V}, I_E=0$			-100	nA
Emitter cut-off current	I_{EB0}	$V_{BE}=-5\text{V}, I_c=0$			-100	nA
DC current gain(note)	h_{FE}	$V_{CE}=-2\text{V}, I_c=-500\text{mA}$	100		320	
Base-emitter on voltage	$V_{BE(on)}$	$V_{CE}=-2\text{V}, I_c=-500\text{mA}$			-1	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c=-1.5\text{A}, I_B=-0.03\text{A}$			-2	V
Output capacitance	C_{ob}	$V_{CB}=-10\text{V}, I_E=0, f=1\text{MHz}$		48		pF
Current gain bandwidth product	f_T	$V_{CE}=-2\text{V}, I_c=-500\text{mA}$		120		MHz

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CLASSIFICATION OF hFE

RANK	O	Y
RANGE	100-200	160-320

TYPICAL CHARACTERISTIC CURVES

